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1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

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Product data sheet

1. General description

High voltage, high speed planar passivated NPN power switching transistor in a SOT428 (DPAK) surface mountable plastic package.

2. Features and benefits

- Fast switching
- · Low thermal resistance
- Surface mountable package
- · Very high voltage capability
- · Very low switching and conduction losses

3. Applications

- DC-to-DC converters
- · High frequency electronic lighting ballasts
- Inverters
- Motor control systems

4. Pinning information

Table 1. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	С
2	С	collector[1]		В
3	Е	emitter		5 - Fa
mb	С	mounting base; connected to collector	1 3 BRAK (SOT 132)	E sym123
			DPAK (SOT428)	

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

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5. Ordering information

Table 2. Ordering information

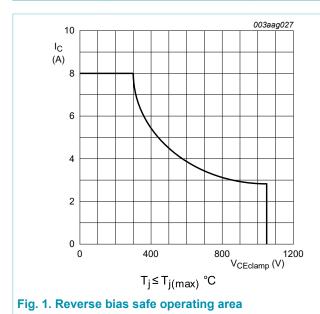
Type number	Package				
	Name	Description	Version		
BUJ302AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

6. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	1050	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
V _{EBO}	emitter-base voltage	$I_C = 0 \text{ A}; I_E = 2 \text{ A}; t_p < 10 \text{ ms}$	-	24	V
I _C	collector current	Fig. 1; Fig. 2; Fig. 3	-	4	Α
I _{CM}	peak collector current		-	8	Α
I _B	base current		-	2	Α
I _{BM}	peak base current		-	4	Α
P _{tot}	total power dissipation	$T_{mb} \le 25 ^{\circ}C; \frac{Fig. 4}{}$	-	80	W
T _{stg}	storage temperature		-65	150	°C
T _j	junction temperature		-	150	°C



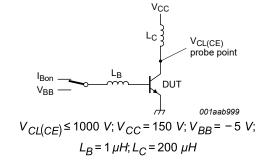
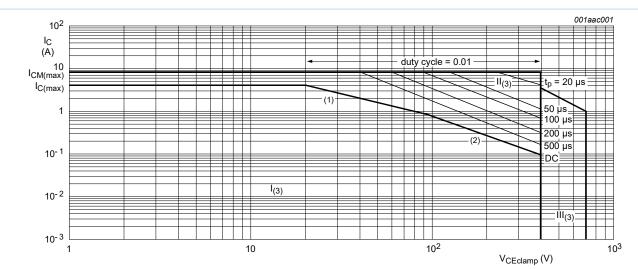


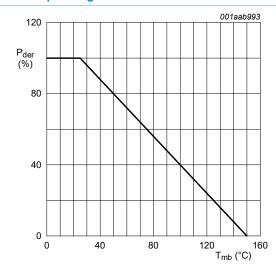
Fig. 2. Test circuit for reverse bias safe operating area

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- 1)Ptot maximum and Ptot peak maximum lines
- 2)Second breakdown limits
- 3) I = Region of permissable DC operation
- II = Extension for repetitive pulse operation
- III = Extension during turn-on in single transistor converters provided that RBE \leq 100 Ω and tp \leq 0.6 μ s

Fig. 3. Forward bias safe operating area for Tmb ≤ 25 °C



$$P_{der} = \frac{P_{tot}}{P_{tot}(25^{\circ}C)} \times 100\%$$

Fig. 4. Normalized total power dissipation as a function of mounting base temperature

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7. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint	-	75	-	K/W

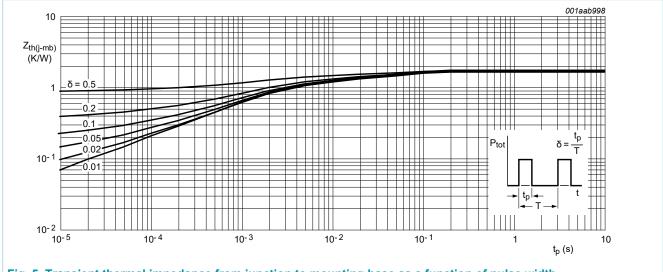


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

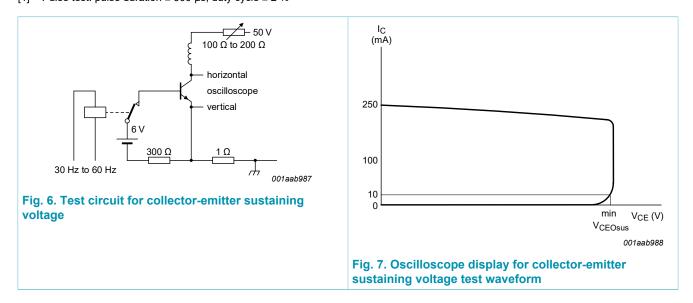
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8. Characteristics

Table 5. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	ecteristics						
I _{CES}	collector-emitter cut-off current (base shorted)	V _{BE} = 0 V; V _{CE} = 1050 V		-	0.2	10	μΑ
I _{CEO}	collector-emitter cut-off current (base open)	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{mb} = 25 \text{ °C}$		-	10	250	mA
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_B = 1 \text{ mA}; I_C = 0 \text{ A}; T_{mb} = 25 \text{ °C}$		15	19	-	V
V_{CEOsus}	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 10 \text{ mA}; L_C = 25 \text{ mH};$ $T_{mb} = 25 \text{ °C}; \underline{\text{Fig. 6}}; \underline{\text{Fig. 7}}$	[1]	400	470	-	V
V _{CEsat}	collector-emitter saturation voltage	$I_C = 1 \text{ A}$; $I_B = 0.2 \text{ A}$; $T_{mb} = 25 \text{ °C}$; <u>Fig. 8</u> ; <u>Fig. 9</u>	[1]	-	0.15	0.5	V
		$I_C = 3.5 \text{ A}$; $I_B = 1 \text{ A}$; $T_{mb} = 25 \text{ °C}$; <u>Fig. 8</u> ; <u>Fig. 9</u>	[1]	-	0.6	1.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3.5 \text{ A}$; $I_B = 1 \text{ A}$; $T_{mb} = 25 \text{ °C}$; Fig. 10	[1]	-	1.1	1.5	V
h _{FE}	DC current gain	I _C = 0.1 A; V _{CE} = 5 V; T _{mb} = 25 °C; Fig. 11	[1]	48	66	100	
		$I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; T_{mb} = 25 ^{\circ}\text{C};$ Fig. 12	[1]	25	42	50	
Dynamic ch	aracteristics						
t _s	storage time	I _C = 2.5 A; I _{Bon} = 0.5 A; I _{Boff} = -0.5 A;		-	-	3.5	μs
t _f	fall time	R_L = 60 Ω; V_{BB} = -5 V; T_{mb} = 25 °C; resistive load; t_p = 300 μs; $Fig. 13$; $Fig. 14$		-	-	500	ns

[1] Pulse test: pulse duration ≤ 300 µs, duty cycle ≤ 2 %



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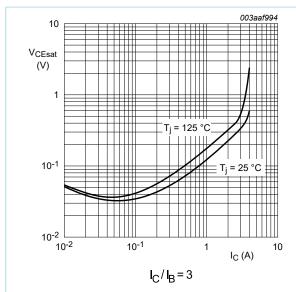


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

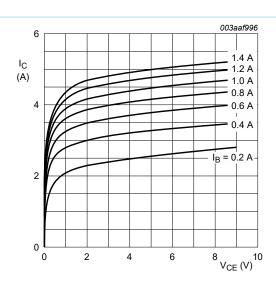


Fig. 9. Collector current as a function of collectoremitter voltage; typical values

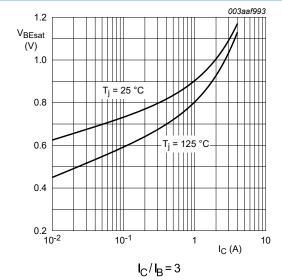


Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

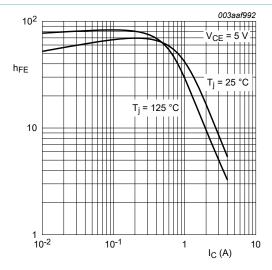


Fig. 11. DC current gain as a function of collector current; typical values

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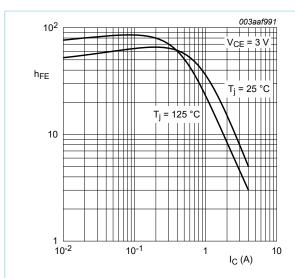


Fig. 12. DC current gain as a function of collector current; typical values

$$\begin{array}{c} V_{CC} \\ \downarrow \\ V_{IM} \\ 0 \\ \downarrow \\ \downarrow \\ T \\ \downarrow \\ 0 \\ 0 \\ 1 \\ ab \\ 989 \end{array}$$

 V_{IM} = -6 to +8 V; V_{CC} = 250 V; t_p = 20 μs ; $\delta = \frac{t_p}{T}$ = 0.01 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig. 13. Test circuit for resistive load switching

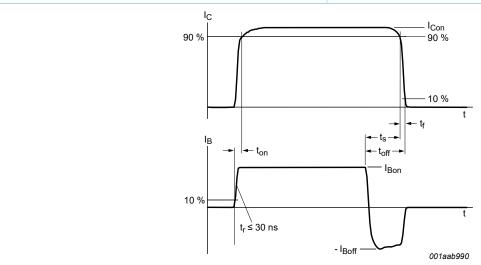


Fig. 14. Switching times waveforms for resistive load

9. Package outline

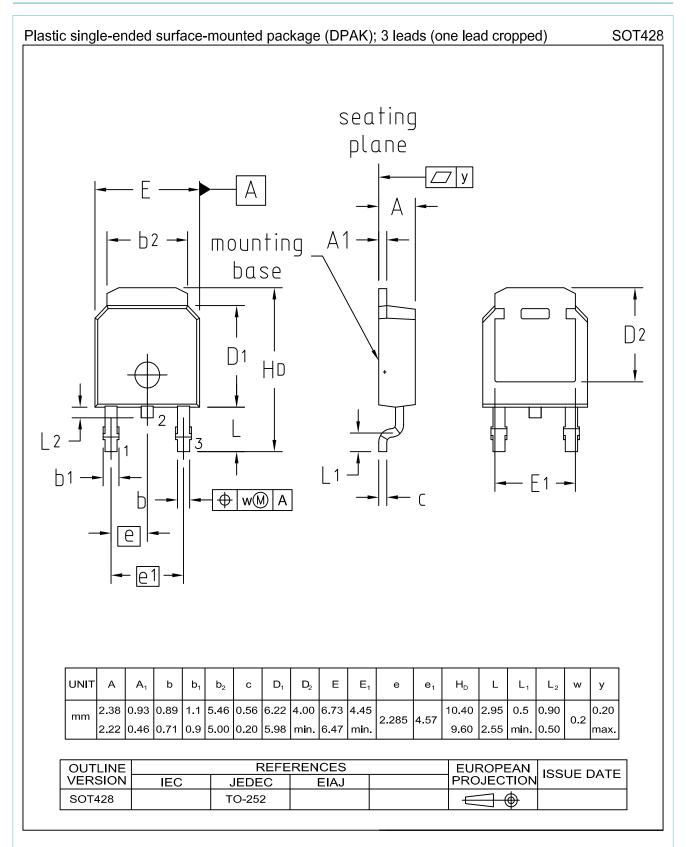


Fig. 15. Package outline DPAK (SOT428)

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10. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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